

IN THE CLAIMS

Please rewrite claims 1, 2, and 6 as follows:

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1. (Once Amended) A semiconductor device comprising a silicon substrate, and a bipolar transistor having a collector well having a first conductivity-type, an internal base region having a second conductivity-type and received in said collector well and an emitter region having said first conductivity-type and received in said internal base region, a first annular isolation trench encircling said collector well, a second annular isolation trench encircling said first annular isolation trench, and an annular diffused region having said second conductivity-type disposed between said first annular isolation trench and said second annular isolation trench while being in contact with said first and second annular isolation trenches.

2. (Once Amended) The semiconductor device as defined in claim 1, wherein said internal base region and said collector well are provided with a base electrode and a collector electrode, and each of said base electrode, said collector electrode and said annular diffused region is provided with a silicide layer on top thereof.

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6. (Once Amended) The semiconductor device as defined in claim 1, wherein said silicon substrate has said second conductivity-type.